

Power MOSFET Demonstrates High Efficiency

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Renesas Technology's RJK0383DPA dual-type power MOSFET achieves an efficiency rating of 91.6% in a synchronous-rectification circuit converting a 12 V DC input to a 1.1 V DC output at 600 kHz switching frequencies. The $5.3 \times 6.2 \times 0.8$ mm WPAK³-packaged device integrates high-side and low-side power MOSFETs and a Schottky barrier diode in DC/DC converters for laptop PCs and communication devices. The MOSFET exhibits a drain-gate load (Q_{gd}) of 1.5 nC at a VDD of 10 V and a typical on-resistance of 3.7 m Ω at 4.5 V.

www.renesas.com
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